

Vishay Semiconductors

High Speed Infrared Emitting Diode, 870 nm, GaAIAs Double Hetero



DESCRIPTION

TSFF5210 is an infrared, 870 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 3/4
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 870 \text{ nm}$
- · High reliability
- · High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 10^{\circ}$
- · Low forward voltage
- · Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 24$ MHz
- · Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- · Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared video data transmission between camcorder and TV set
- Free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Smoke-automatic fire detectors

PRODUCT SUMMARY				
COMPONENT	l _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)
TSFF5210	180	± 10	870	15

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSFF5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	
Note				

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	5	V
Forward current		١ _F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA
Surge forward current	t _p = 100 μs	I _{FSM}	1	А
Power dissipation		Pv	180	mW
Junction temperature		Тj	100	°C
Operating temperature range		T _{amb}	- 40 to + 85	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq$ 5 s, 2 mm from case	T _{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	230	K/W

Note

T_{amb} = 25 °C, unless otherwise specified



HALOGEN

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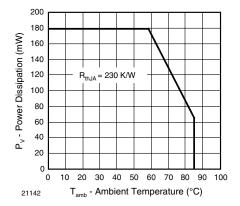


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

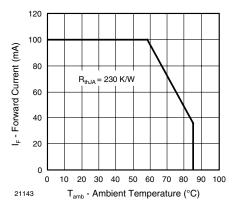


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
	I _F = 100 mA, t _p = 20 ms	V _F		1.5	1.8	V
Forward voltage	I _F = 1 A, t _p = 100 μs	V _F		2.3		V
Temperature coefficient of V_F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		125		pF
Dediest interails	I _F = 100 mA, t _p = 20 ms	le	120	180	360	mW/sr
Radiant intensity	I _F = 1 A, t _p = 100 μs	l _e		1800	10	mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		50		mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I _F = 100 mA	λρ		870		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I _F = 100 mA	tr		15		ns
Fall time	I _F = 100 mA	t _f		15		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		24		MHz
Virtual source diameter		d		3.7		mm

Note

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BASIC CHARACTERISTICS

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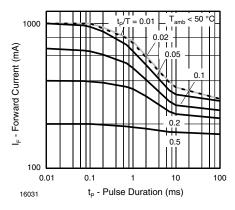


Fig. 3 - Pulse Forward Current vs. Pulse Duration

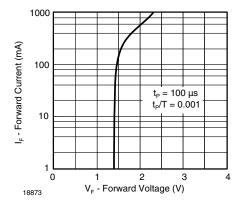


Fig. 4 - Forward Current vs. Forward Voltage

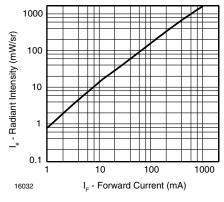


Fig. 5 - Radiant Intensity vs. Forward Current

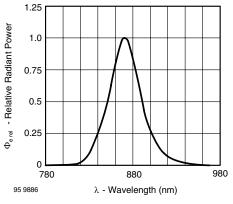


Fig. 6 - Relative Radiant Power vs. Wavelength

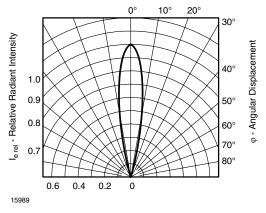


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

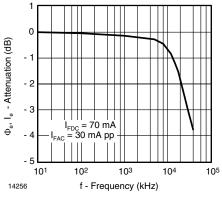
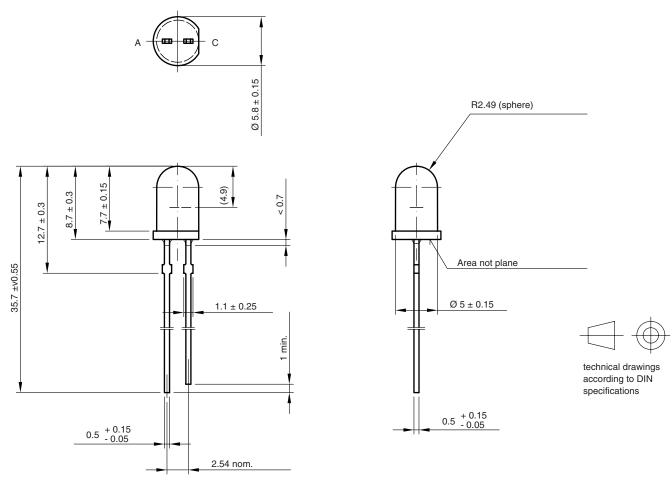


Fig. 8 - Attenuation vs. Frequency

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PACKAGE DIMENSIONS in millimeters



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